

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Silicon PIN Diode

- Optimized for antenna switches in hand held applications
- Very low capacitance at zero volts reverse bias at frequencies above 1GHz (typ. 0.19 pF)
- Low forward resistance (typ. 0.8Ω @ I_F = 10mA)
- Very low signal distortion
- Pb-free (RoHS compliant) package





BAR89-02LRH



Туре	Package	Configuration	L S(nH)	Marking
BAR89-02LRH	TSLP-2-7	single, leadless	0.4	R

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V_{R}	80	V	
Forward current	I _F	100	mA	
Total power dissipation	P _{tot}	250	mW	
<i>T</i> _S ≤ 133°C				
Junction temperature	T_{i}	150	°C	
Operating temperature range	T_{op}	-55 125		
Storage temperature	$T_{ m stg}$	-55 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 65	K/W

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 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	·	•			•
Breakdown voltage	$V_{(BR)}$	80	-	-	V
$I_{(BR)} = 5 \mu A$					
Reverse current	I_{R}	-	-	50	nA
V _R = 60 V					
Forward voltage	V_{F}				V
$I_{\rm F}$ = 10 mA		-	0.83	0.9	
$I_{\rm F}$ = 100 mA		-	0.95	1.1	



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

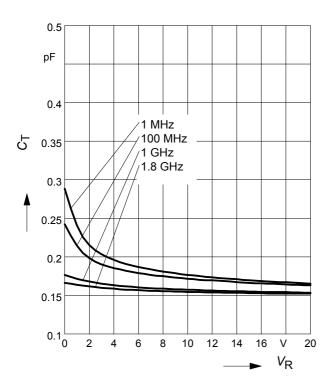
Parameter	Symbol		Values		
		min.	typ.	max.	
AC Characteristics	_				
Diode capacitance	C _T				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		-	0.25	0.35	
$V_{R} = 0 \text{ V}, f = 100 \text{ MHz}$		-	0.25	-	
$V_{R} = 0 \text{ V}, f = 1 \text{ GHz}$		-	0.19	-	
$V_{R} = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	0.18	-	
Reverse parallel resistance	R_{P}				kΩ
$V_{R} = 0 \text{ V}, f = 100 \text{ MHz}$		-	35	-	
$V_{R} = 0 \text{ V}, f = 1 \text{ GHz}$		-	5	-	
$V_{R} = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	3.5	-	
Forward resistance	r_{f}				Ω
$I_{\rm F}$ = 1 mA, f = 100 MHz		-	3	-	
$I_{\rm F}$ = 5 mA, f = 100 MHz		-	1.2	-	
$I_{\rm F}$ = 10 mA, f = 100 MHz		-	0.8	1.5	
Charge carrier life time	τ _{rr}	-	800	-	ns
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 6 mA, measured at $I_{\rm R}$ = 3 mA,					
R_{L} = 100 Ω					
I-region width	W _I	-	19	-	μm
Insertion loss ¹⁾	/ _L				dB
$I_{\rm F}$ = 1 mA, f = 1.8 GHz		-	0.23	-	
$I_{\rm F}$ = 5 mA, f = 1.8 GHz		-	0.1	_	
$I_{\rm F}$ = 10 mA, f = 1.8 GHz		-	0.08	_	
Isolation ¹⁾	I _{SO}				
$V_{R} = 0 \text{ V}, f = 0.9 \text{ GHz}$		-	19	_	
$V_{R} = 0 \text{ V}, f = 1.8 \text{ GHz}$		-	14	_	
$V_{R} = 0 \text{ V}, f = 2.45 \text{ GHz}$		-	11	_	

¹BAR89-02LRH in series configuration, $Z = 50\Omega$



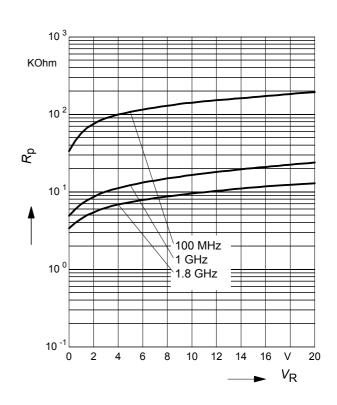
Diode capacitance $C_T = f(V_R)$

f = Parameter



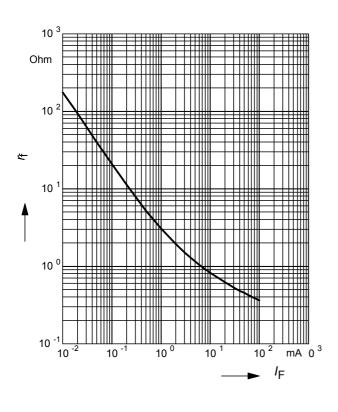
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



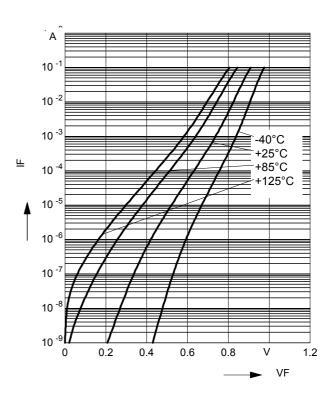
Forward resistance $r_f = f(I_F)$

f = 100MHz



Forward current $I_F = f(V_F)$

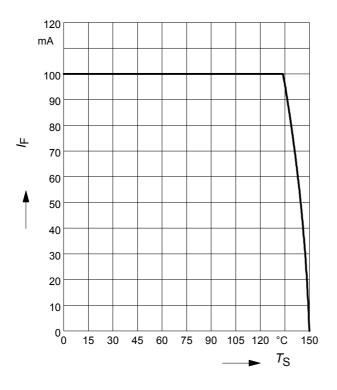
 T_A = Parameter





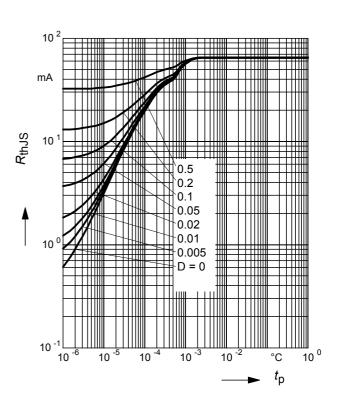
Forward current $I_F = f(T_S)$

BAR89-02LRH



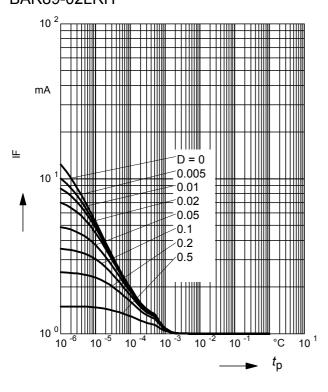
Permissible Puls Load R_{thJS} = $f(t_{\text{p}})$

BAR89-02LRH



Permissible Pulse Load

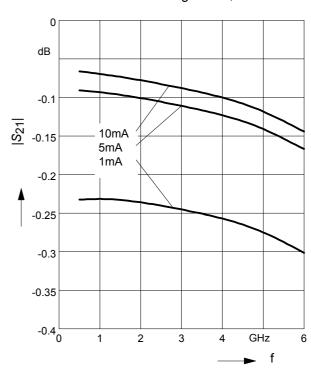
 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$ BAR89-02LRH



Insertion loss $I_{L} = -|S_{21}|^2 = f(f)$

 $I_{\rm F}$ = Parameter

BAR89-02LRH in series configuration, $Z = 50\Omega$

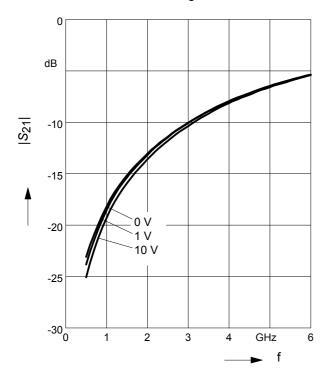




Isolation $I_{SO} = -|S_{21}|^2 = f(f)$

 V_{R} = Parameter

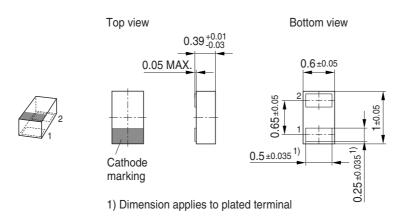
BAR89-02LRH in series configuration, $Z = 50\Omega$



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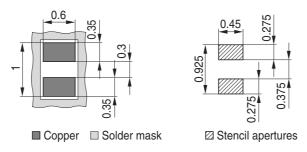


Package Outline

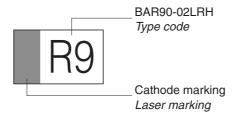


Foot Print

For board assembly information please refer to Infineon website "Packages"

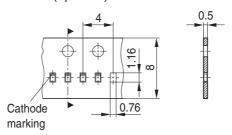


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel Reel ø330 mm = 50.000 Pieces/Reel (optional)



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